HEF40240B

Octal inverting buffers with 3-state outputs

Rev. 5 — 15 November 2011 Product data sheet

1. General description

The HEF40240B is an octal inverting buffer with 3-state outputs. It features output stages with high current output capability suitable for driving highly capacitive loads.

The 3-state outputs are controlled by the output enable inputs n$\overline{OE}$. A HIGH on n$\overline{OE}$ causes the outputs to assume a high-impedance OFF-state. The device also features hysteresis on all inputs to improve noise immunity. Schmitt-trigger action makes the inputs highly tolerant to slow input rise and fall times.

The HEF40240B is pin and functionally compatible with the TTL ‘240’ device.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

2. Features and benefits

- Tolerant of slow input rise and fall times
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from −40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. Ordering information

Table 1. Ordering information

All types operate from −40 °C to +85 °C.

Type number	Package		
	Name	Description	Version
HEF40240BP	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1
HEF40240BT	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1

4. Functional diagram

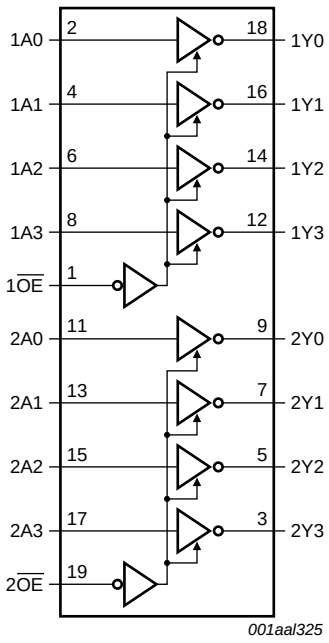


Fig 1. Functional diagram

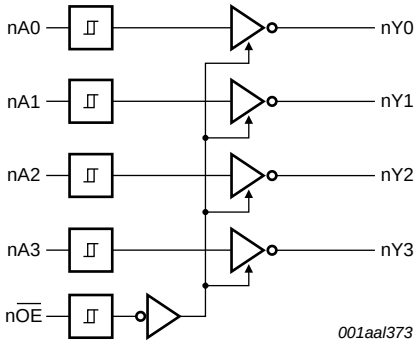


Fig 2. Logic diagram

5. Pinning information

5.1 Pinning

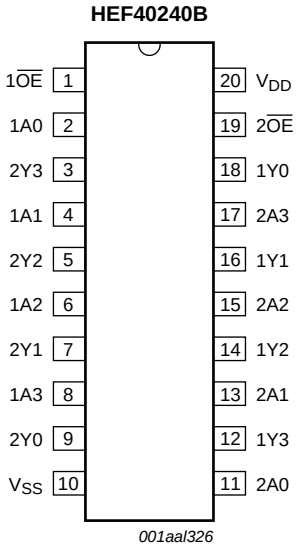


Fig 3. Pin configuration DIP20

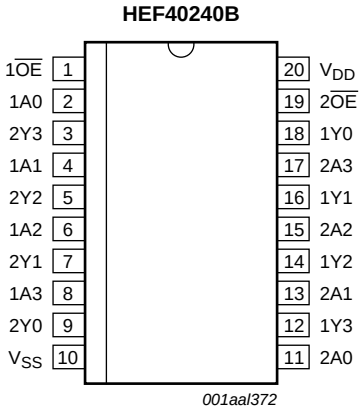


Fig 4. Pin configuration SO20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}$	1	output enable input (active LOW)
1A0, 1A1, 1A2, 1A3	2, 4, 6, 8	data input
V_{SS}	10	ground (0 V)
2Y0, 2Y1, 2Y2, 2Y3	9, 7, 5, 3	data output
2A0, 2A1, 2A2, 2A3	11, 13, 15, 17	data input
V_{DD}	20	supply voltage
1Y0, 1Y1, 1Y2, 1Y3	18, 16, 14, 12	data output
$2\overline{OE}$	19	output enable input (active LOW)

6. Functional description

Table 3. Function table[1]

Inputs		Output
nAn	**$n\overline{OE}$**	**nYn**
H	L	L
L	L	H
X	H	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DD}	supply voltage			−0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{DD} + 0.5$ V		-	±10	mA
V_I	input voltage			−0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{DD} + 0.5$ V		-	±10	mA
I_I	input leakage current	into any input		-	±10	mA
I_O	output current	sink or source current	[1]	-	±25	mA
I_{DD}	supply current	to any supply terminal		-	±100	mA
T_{stg}	storage temperature			−65	+150	°C
T_{amb}	ambient temperature			−40	+85	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +85 °C				
		DIP20 package	[2]	-	750	mW
		SO20 package	[3]	-	500	mW
P	power dissipation	per output		-	100	mW

[1] See Figure 6.

[2] For DIP20 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] For SO20 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

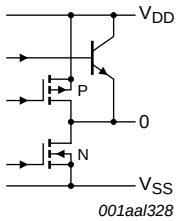
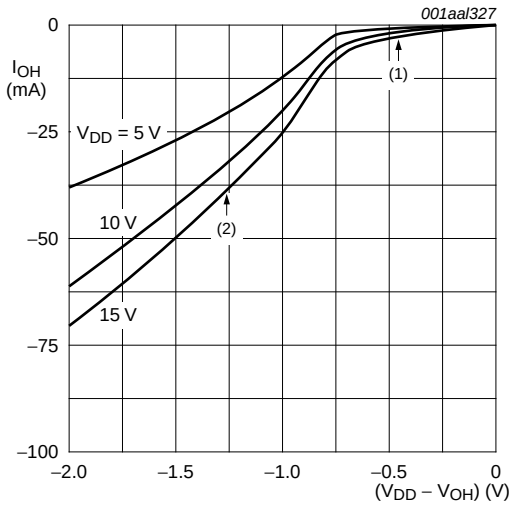


Fig 5. Schematic diagram of a buffer output stage



(1) P-channel MOS transistor conducting.

(2) P-channel MOS transistor and bipolar NPN transistor conducting.

Fig 6. Typical output source current characteristic

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	−40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{DD} = 5 V	-	-	3.75	µs/V
		V_{DD} = 10 V	-	-	0.5	µs/V
		V_{DD} = 15 V	-	-	0.08	µs/V

9. Static characteristics

Table 6. Static characteristics

V_{SS} = 0 V; V_I = V_{SS} or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T_{amb} = –40 °C		T_{amb} = +25 °C		T_{amb} = +85 °C		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$\|I_O\|$ < 1 μA	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$\|I_O\|$ < 1 μA	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_H	hysteresis voltage	for any input	5 V	-	-	-	220.0	-	-	mV
			10 V	-	-	-	250.0	-	-	mV
			15 V	-	-	-	320.0	-	-	mV
V_{OH}	HIGH-level output voltage	$\|I_O\|$ < 1 μA	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$\|I_O\|$ < 1 μA	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	V_O = 3.6 V	5 V	-	–9.3	–24.0	–10.0	-	–10.7	mA
		V_O = 8.4 V	10 V	-	–14.4	–46.0	–15.0	-	–15.0	mA
		V_O = 13.2 V	15 V	-	–19.5	–62.0	–20.0	-	–19.8	mA
		V_O = 4.6 V	5 V	-	–0.75	–1.2	–0.6	-	–0.45	mA
		V_O = 9.5 V	10 V	-	–1.85	–3.0	–1.5	-	–1.1	mA
		V_O = 13.5 V	15 V	-	–14.5	–50.0	–15.0	-	–15.5	mA
I_{OL}	LOW-level output current	V_O = 0.4 V	5 V	2.9	-	2.3	5.4	1.75	-	mA
		V_O = 0.5 V	10 V	9.5	-	7.6	17.0	5.50	-	mA
		V_O = 1.5 V	15 V	30.0	-	25.0	45.0	19.0	-	mA
I_I	input leakage current		15 V	-	±0.3	-	±0.3	-	±1.0	μA
I_{DD}	supply current	I_O = 0 A	5 V	-	4	-	4	-	30	μA
			10 V	-	8	-	8	-	60	μA
			15 V	-	16	-	16	-	120	μA
I_{OZ}	OFF-state output current		15 V	-	1.6	-	1.6	-	12	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	pF

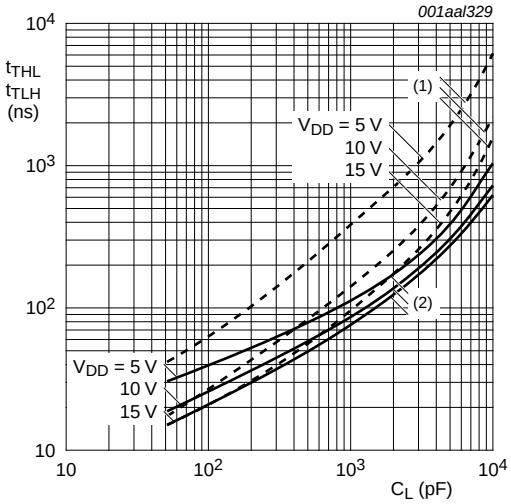
10. Dynamic characteristics

Table 7. Dynamic characteristics

V_{SS} = 0 V; T_{amb} = 25 °C; for test circuit see Figure 10; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}		Extrapolation formula	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	nAn to nYn; see Figure 8	5 V	[1]	83 ns + (0.24 ns/pF)C_L	-	95	190	ns
			10 V		35 ns + (0.10 ns/pF)C_L	-	40	80	ns
			15 V		26 ns + (0.07 ns/pF)C_L	-	30	60	ns
t_{PLH}	LOW to HIGH propagation delay	nAn to nYn; see Figure 8	5 V	[1]	82 ns + (0.06 ns/pF)C_L	-	85	170	ns
			10 V		38 ns + (0.03 ns/pF)C_L	-	40	80	ns
			15 V		29 ns + (0.02 ns/pF)C_L	-	30	60	ns
t_{PHZ}	HIGH to OFF-state propagation delay	$n\overline{OE}$ to nYn; nYn is HIGH; see Figure 9	5 V			-	70	140	ns
			10 V			-	35	70	ns
			15 V			-	30	60	ns
t_{PLZ}	LOW to OFF-state propagation delay	$n\overline{OE}$ to nYn; nYn is LOW; see Figure 9	5 V			-	75	150	ns
			10 V			-	40	80	ns
			15 V			-	30	60	ns
t_{PZH}	OFF-state to HIGH propagation delay	$n\overline{OE}$ to nYn; nYn goes HIGH; see Figure 9	5 V			-	80	160	ns
			10 V			-	35	70	ns
			15 V			-	30	60	ns
t_{PZL}	OFF-state to LOW propagation delay	$n\overline{OE}$ to nYn; nYn goes LOW; see Figure 9	5 V			-	90	180	ns
			10 V			-	40	80	ns
			15 V			-	30	60	ns
t_{THL}	HIGH to LOW output transition time	see Figure 7 and Figure 8	5 V			-	40	80	ns
			10 V			-	20	40	ns
			15 V			-	15	30	ns
t_{TLH}	LOW to HIGH output transition time	see Figure 7 and Figure 8	5 V			-	30	60	ns
			10 V			-	20	40	ns
			15 V			-	15	30	ns

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).



(1) t_{THL}.

(2) t_{TLH}.

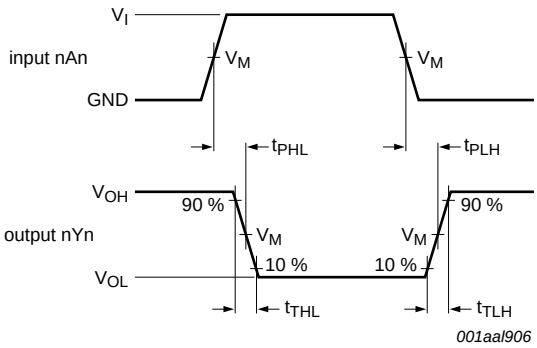
Fig 7. Output transition times as a function of the load capacitance

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. V_{SS} = 0 V; $t_r = t_f \leq 20$ ns; T_{amb} = 25 °C.

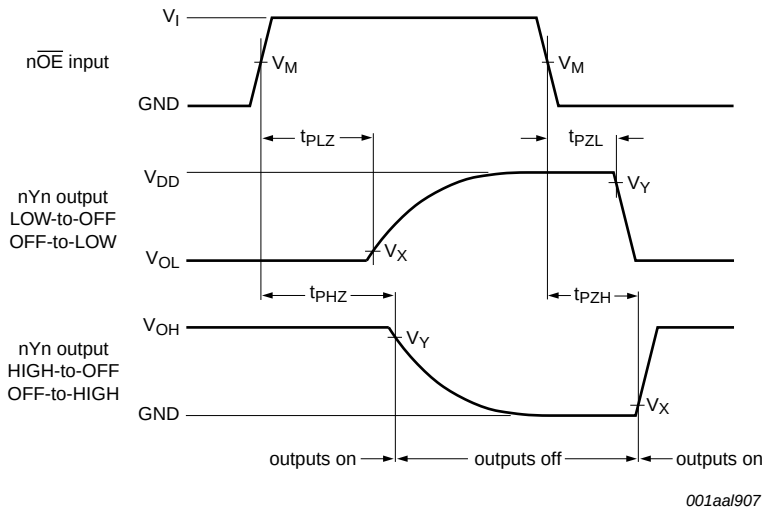
Symbol	Parameter	V_{DD}	Typical formula for P_D (µW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 4250 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,
		10 V	$P_D = 17000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz,
		15 V	$P_D = 46000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.

11. Waveforms



Measurement points are given in Table 9, V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. Waveforms showing propagation and transition delays

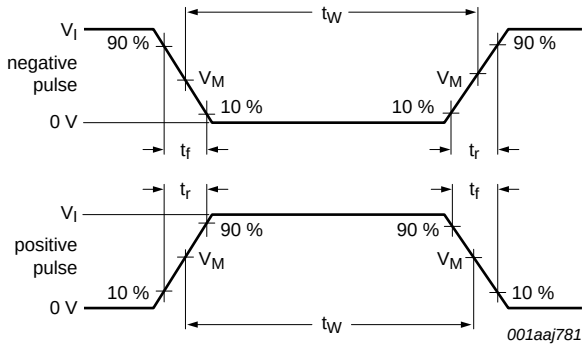


Measurement points are given in Table 9, V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

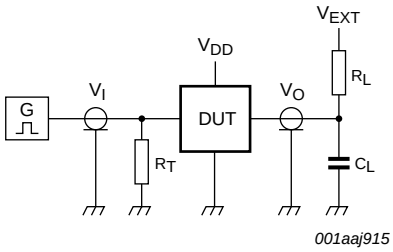
Fig 9. 3-state enable and disable times

Table 9. Measurement points

Supply voltage	Input	Output		
V_{DD}	V_M	V_M	V_X	V_Y
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$	$0.1V_{DD}$	$0.9V_{DD}$



a. Input waveforms



b. Test circuit

For test data see Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

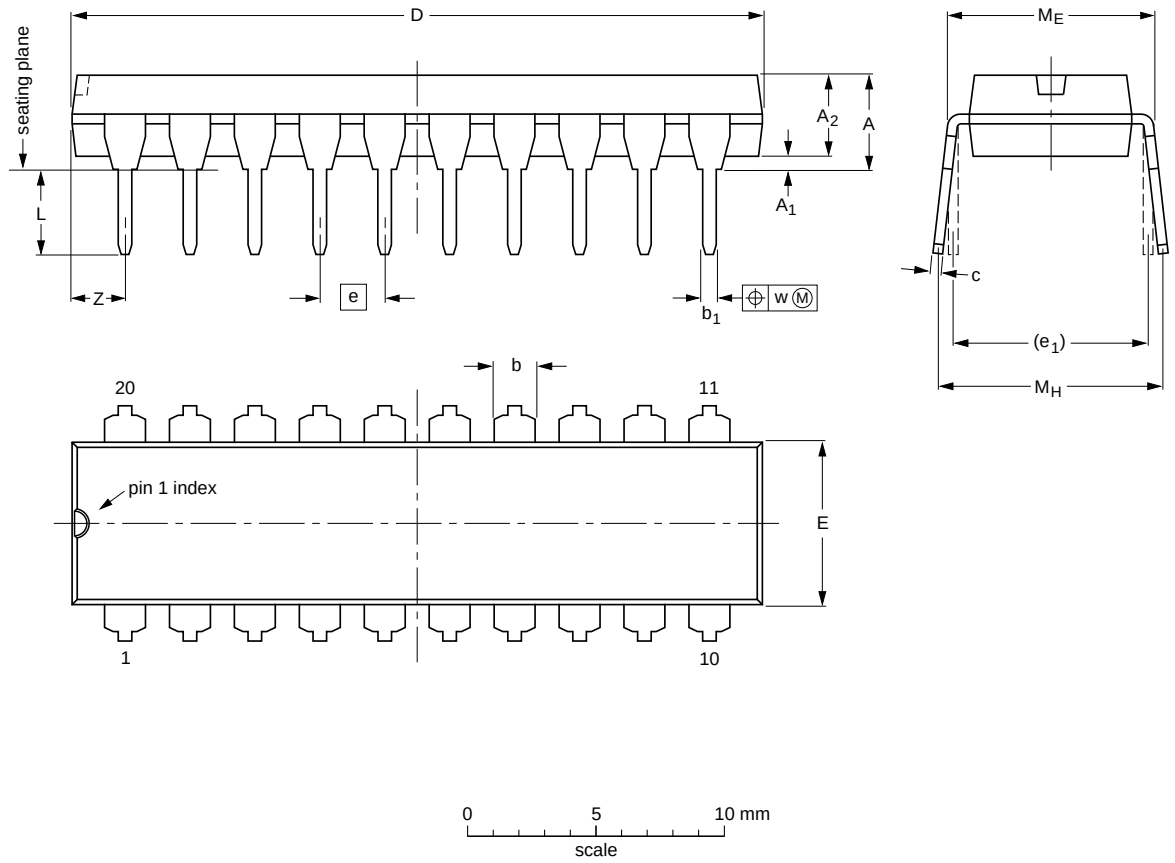
Fig 10. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{DD}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF	1 kΩ	open	V_{DD}	GND

12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil) **SOT146-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

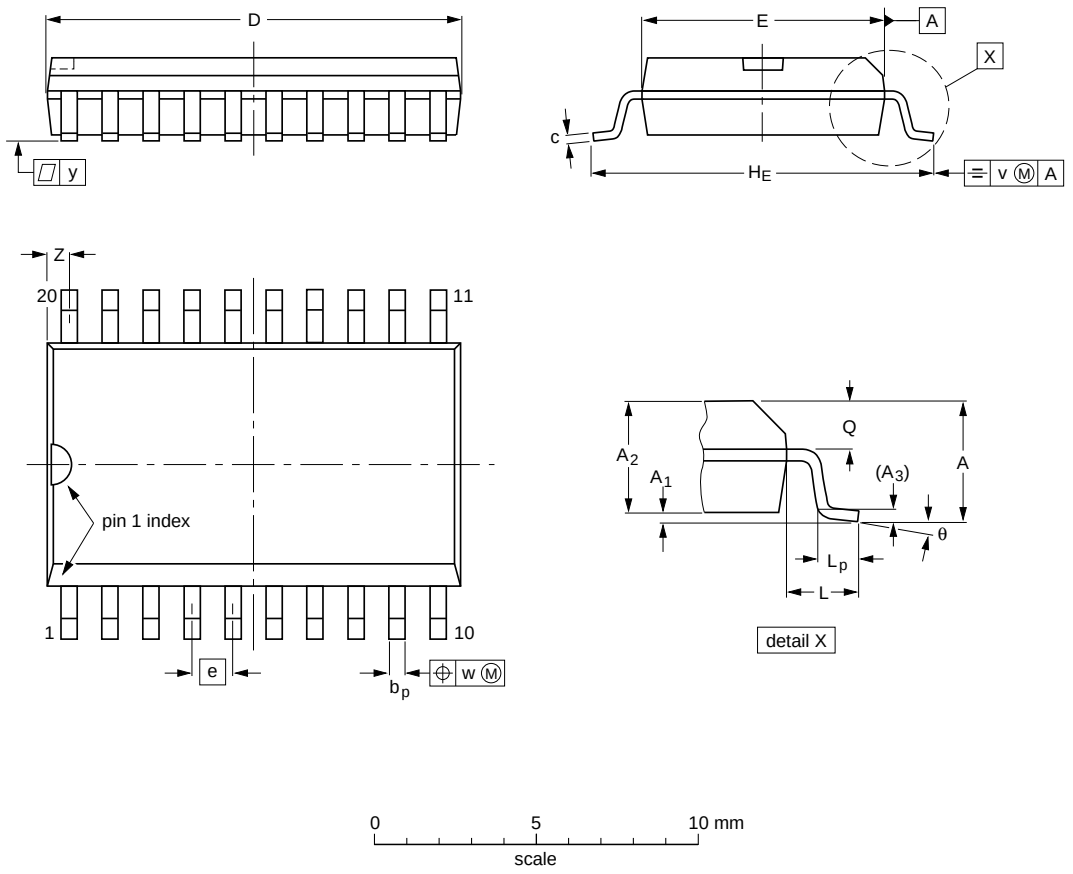
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT146-1		MS-001	SC-603			~~99-12-27~~ 03-02-13

Fig 11. Package outline SOT146-1 (DIP20)

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 12. Package outline SOT163-1 (SO20)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test
MOS	Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF40240B v.5	20111115	Product data sheet	-	HEF40240B v.4
Modifications:	• Section Applications removed • Table 6: I_{OH} minimum values changed to maximum			
HEF40240B v.4	20100420	Product data sheet	-	HEF40240B_CNV v.3
HEF40240B_CNV v.3	19950101	Product specification	-	HEF40240B_CNV v.2
HEF40240B_CNV v.2	19950101	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

17. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 15 November 2011
Document identifier: HEF40240B